

UHF power LDMOS transistor - Application: PHS ; Description: Basestation LDMOS RF POWER Transistor ; Efficiency: 35@CW20@PHS %; Frequency: HF - 2200 MHz; Load power: 30 (CW) / 10 (PHS) W; Operating voltage: 26 VDC; Power gain: 13.5 (CW) / 16 (PHS) dB, MOSFET LDMOS TNS

Manufacturers	<u><a href="#">NXP Semiconductor</a></u>
Package/Case	LDMOST-3
Product Type	Transistors
RoHS	Rohs
Lifecycle	



Images are for reference only

Please submit RFQ for BLF3G21-30 or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

## General Description

BLF3G21-30 is a specific model number of a power transistor, manufactured by NXP Semiconductors. It belongs to the BLF3G series of high-power transistors, which are designed for use in high-frequency amplifiers and power amplifiers.

## Features

Frequency range: 2110-2170 MHz

Output power: 30 Watts

Efficiency: 48%

Gain: 16 dB

Operating voltage: 32V



### Related Products



#### [BLT50](#)

NXP Semiconductor  
SOT-223



#### [BLF574](#)

NXP Semiconductor  
TO-59



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NXP Semiconductor  
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